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Intellectual Property Law



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Linda H. Liu

January 27, 2006

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Re: Title: HIGH ASPECT RATIO CONTACT STRUCTURE WITH REDUCED
SILICON CONSUMPTION
Letters Patent No. 6,858,904
Issued: February 22, 2005
Our Reference: MICRON.240A

Certificate

FEB 01 2006

of Correction

Dear Sir:

The Applicant respectfully submits the enclosed Certificate of Correction to correct an error noted in Claim 10 of the above-referenced patent. The Applicant has amended Claim 10 in an office action filed January 10, 2003 in which the Applicant added the limitation "wherein a substantial portion of the titanium silicide is interspersed in the titanium before the conductive contact layer is deposited on the upper surface of the silicon substrate over the junction region.". However, this limitation was inadvertently left out of reproductions of Claim 10 in subsequent amendments the Applicant filed. As a consequence, Claim 10 in the above issued patent does not contain the above noted limitation. Thus, the Applicant is submitting a Certificate of Correction to correct this error.

As the errors cited in the Certificate of Correction were incurred through the fault of the Applicant, enclosed is our check in the amount of \$100. Please charge any additional fees to our Deposit Account No. 11-1410.

Respectfully submitted,

Knobbe, Martens, Olson & Bear, LLP

Linda H. Liu
Registration No. 51,240
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Enclosures
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UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,858,904 B2

DATED : February 22, 2005

INVENTOR(S): Derraa et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

At Column 8, Line 2, in Claim 10, after "region," please add -- wherein a substantial portion of the titanium silicide is interspersed in the titanium before the conductive contact layer is deposited on the upper surface of the silicon substrate over the junction region, --

MAILING ADDRESS OF SENDER:

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PATENT NO. 6,858,904 B2

January 27, 2006

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